Central™
Semiconductor Corp.

PROCESS CPQ150

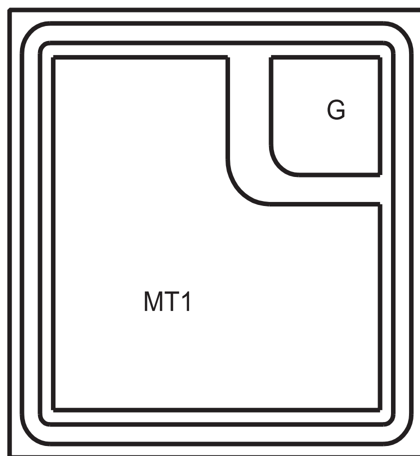
Triac

16 Amp, 600 Volt Triac Chip

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	150 MILS x 150 MILS
Die Thickness	8.6 MILS ± 0.6 MILS
MT1 Bonding Pad Area	68.9 MILS x 118 MILS
Gate Bonding Pad Area	39.4 MILS x 39.4 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

GEOMETRY



BACKSIDE MT2

R0

GROSS DIE PER 4 INCH WAFER

466

PRINCIPAL DEVICE TYPES

CQ220-16B Series

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R0 (13-February 2003)